



100V N-Channel MOSFET

Voltage

100 V

Current

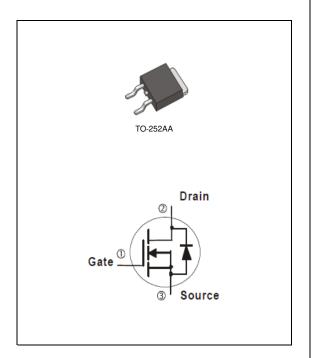
6 A

Features

- R_{DS(ON)}, V_{GS}@10V,I_D@3A<310mΩ
- $\bullet \ \ R_{DS(ON)}, \ V_{GS}@4.5V, I_{D}@1.5A{<}320m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

- Case: TO-252AA Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	6	А	
	T _C =100°C		3.8		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	12		
Power Dissipation	T _C =25°C	Po	25	14/	
	T _C =100°C		10	W	
Continuous Drain Current	T _A =25°C	I _D	1.7	Α	
	T _A =70°C		1.4	Α	
Power Dissipation	T _A =25°C	0	2.0	W	
Power Dissipation	T _A =70°C	Po	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	1.8	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	5.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	2.06	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =3.0A	-	280	310	mΩ
		V _{GS} =4.5V,I _D =1.5A	-	290	320	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =80V, V_{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 4)						
Total Gate Charge	Q_g	V _{DS} =50V, I _D =3A, V _{GS} =10V ^(Note 1,2)	-	9.1	-	nC
Gate-Source Charge	Q_gs		-	2.1	-	
Gate-Drain Charge	Q_gd	V _{GS} =10V	-	1.4	-	
Input Capacitance	Ciss	V 20V V 0V	-	508	-	pF
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, I_{S} =1.0MHZ	-	29	-	
Reverse Transfer Capacitance	Crss	I=1.UIVINZ	-	18	-	
Turn-On Delay Time	td _(on)	\/ F0\/ OA	-	2	-	
Turn-On Rise Time	t _r	$V_{DD}=50V, I_{D}=3A, V_{GS}=10V, R_{G}=6\Omega$	-	21	-	ns
Turn-Off Delay Time	td _(off)	(Note 1,2)	-	12	-	
Turn-Off Fall Time	t _f		-	19	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	ı				6	Α
Diode Forward Current	I _S		-	-	b	A
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.78	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =6A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

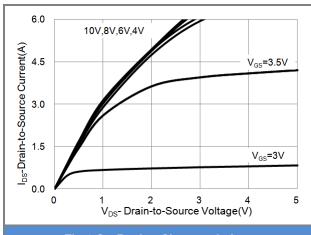


Fig.1 On-Region Characteristics

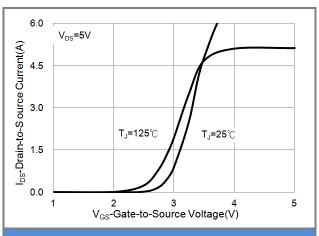


Fig.2 Transfer Characteristics

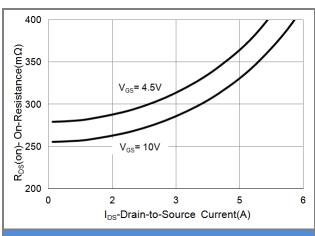


Fig.3 On-Resistance vs. Drain Current

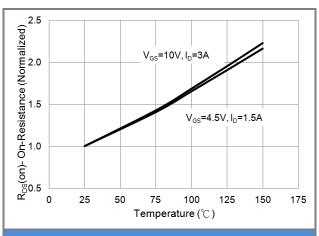


Fig.4 On-Resistance vs. Junction temperature

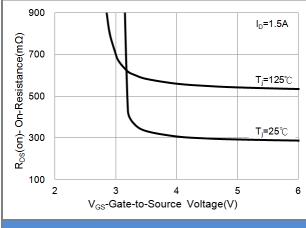


Fig.5 On-Resistance Variation with VGS.

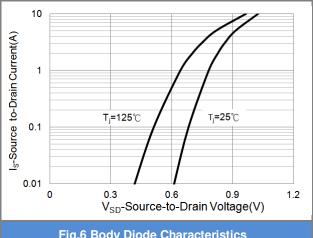


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

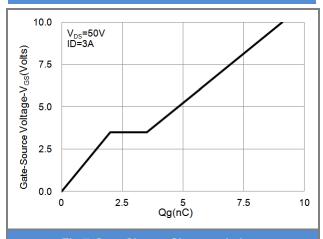


Fig.7 Gate-Charge Characteristics

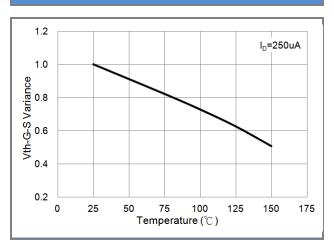


Fig.9 Threshold Voltage Variation with Temperature

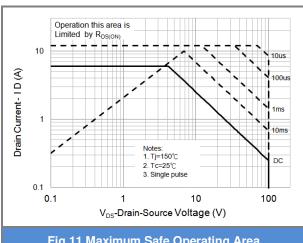


Fig.11 Maximum Safe Operating Area

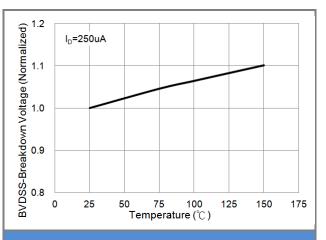


Fig.8 Breakdown Voltage Variation vs. Temperature

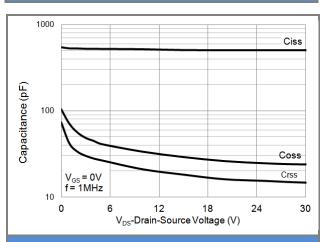


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

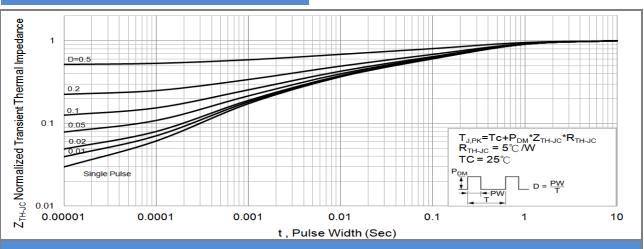
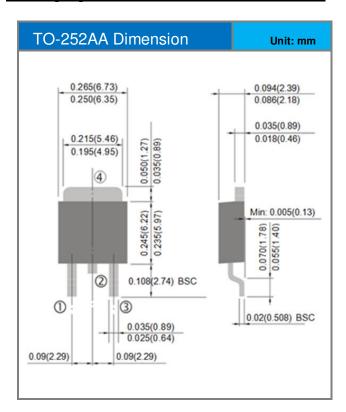


Fig.12 Normalized Thermal Transient Impedance





Packaging Information



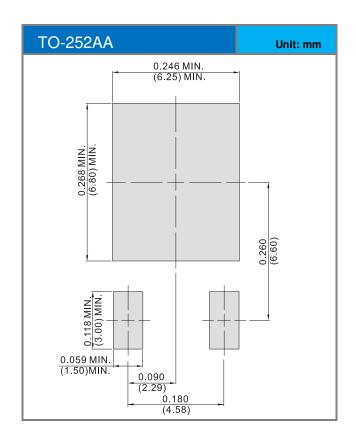




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD6N10A_L2_00001	TO-252AA	3,000pcs / 13" reel	D6N10A	Halogen free

MOUNTING PAD LAYOUT







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